ABSTRACT OF THE DISCLOSURE

A novel process for producing a semiconductor article is disclosed which comprises steps of preparing a first substrate constituted of a silicon substrate, a nonporous semiconductor layer formed on the silicon substrate, and an ion implantation layer formed in at least one of the silicon substrate and the nonporous semiconductor layer; bonding the first substrate to a second substrate to obtain a multiple layer structure with the nonporous semiconductor layer placed inside; separating the multiple layer structure at the ion implantation layer; and removing the ion implantation layer remaining on the separated second substrate.

This Sheet Has Been Replaced

THIS SHEET HAS BEEN REPLACED